



General Description

The IRFR120NTRPBF use advanced SGT MOSFET technology to provide low RDS(ON), low gate charge, fast switching and excellent avalanche characteristics.

This device is specially designed to get better ruggedness and suitable to use in.



TO-252-2L

General Features

$V_{DS} = 100V$ $I_D = 12A$

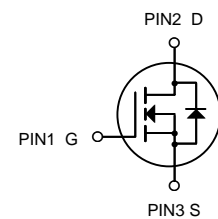
$R_{DS(ON)} < 120m\Omega @ V_{GS}=10V$

Applications

Consumer electronic power supply

Motor control

Synchronous-rectification



N-Channel MOSFET

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
IRFR120NTRPBF	TO-252-2L	12N10 XXXXX	2500

Absolute Maximum Ratings at $T_j=25^\circ C$ unless otherwise noted

Symbol	Parameter	Value	Unit
VDS	Drain source voltage	100	V
VGS	Gate source voltage	± 20	V
ID	Continuous drain current ¹⁾	12	A
ID, pulse	Pulsed drain current ²⁾	24	A
P _D	Power dissipation ³⁾	17	W
EAS	Single pulsed avalanche energy ⁴⁾	1.2	mJ
Tstg, T _j	Operation and storage temperature	-55 to 150	°C
R θ JC	Thermal resistance, junction-case	6.6	°C/W
R θ JA	Thermal resistance, junction-ambient ⁵⁾	62	°C/W



Electrical Characteristics $T_c=25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	100	110	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 100V, V_{GS} = 0V$	-	-	1	μA
I_{GSS}	Gate to Body Leakage Current	$V_{DS} = 0V, V_{GS} = \pm 20V$	-	-	± 100	nA
On Characteristics ^{note3}						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\mu A$	1.0	1.8	3.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance ^{note2}	$V_{GS} = 10V, I_D = 3A$	-	95	120	m Ω
Dynamic Characteristics ^{note4}						
C_{iss}	Input Capacitance	$V_{DS} = 50V, V_{GS} = 0V,$ $f = 1.0MHz$	-	196	-	pF
C_{oss}	Output Capacitance		-	25.9	-	pF
C_{rss}	Reverse Transfer Capacitance		-	21.4	-	pF
Q_g	Total Gate Charge	$V_{DS} = 50V, I_D = 3A,$ $V_{GS} = 10V$	-	4.3	-	nC
Q_{gs}	Gate-Source Charge		-	3.5	-	nC
Q_{gd}	Gate-Drain("Miller") Charge		-	3.1	-	nC
Switching Characteristics ^{note4}						
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 50V, I_{DS}=3A$ $R_G = 2\Omega, V_{GEN} = 10V$	-	14.7	-	ns
t_r	Turn-On Rise Time		-	3.5	-	ns
$t_{d(off)}$	Turn-Off Delay Time		-	20.9	-	ns
t_f	Turn-Off Fall Time		-	2.7	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain to Source Diode Forward Current ^{note2}		-	-	4.5	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	12	A
V_{SD}	Drain to Source Diode Forward Voltage ^{note3}	$V_{GS} = 0V, I_S = 3A$	-	-	1.3	V
t_{rr}	Body Diode Reverse Recovery Time	$V_{GS} = 0V, I_F = 3A,$ $di/dt = 100A/\mu s$	-	32.1	-	ns
Q_{rr}	Body Diode Reverse Recovery Time Charge		-	39.4	-	nC
I_{rrm}	Peak Reverse Recovery Current		-	2.1	-	A

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production
5. $V_{DD}=50$ V, $R_G=50$ Ω , $L=0.3$ mH, starting $T_j=25$ $^\circ\text{C}$



Typical Performance Characteristics

Figure 1: Output Characteristics

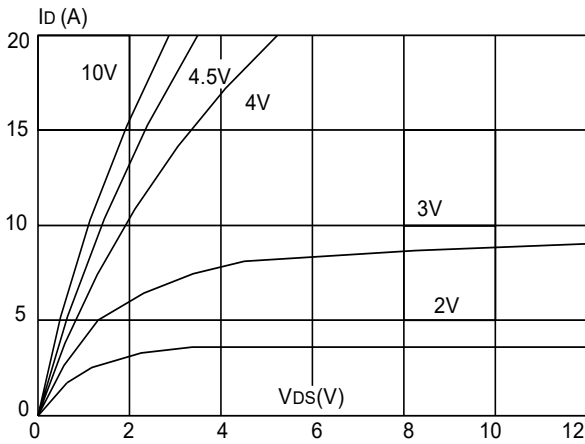


Figure 2: Typical Transfer Characteristics

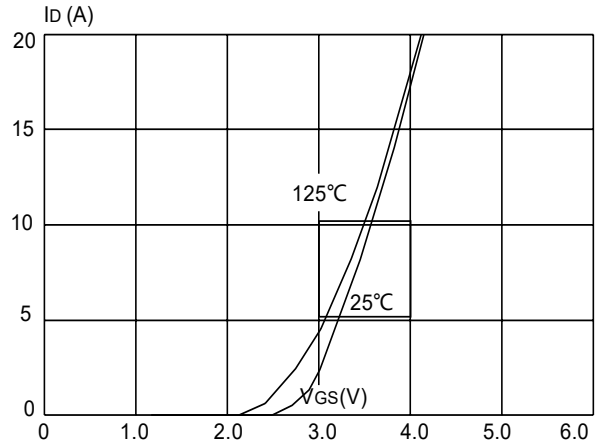


Figure 3: On-resistance vs. Drain Current

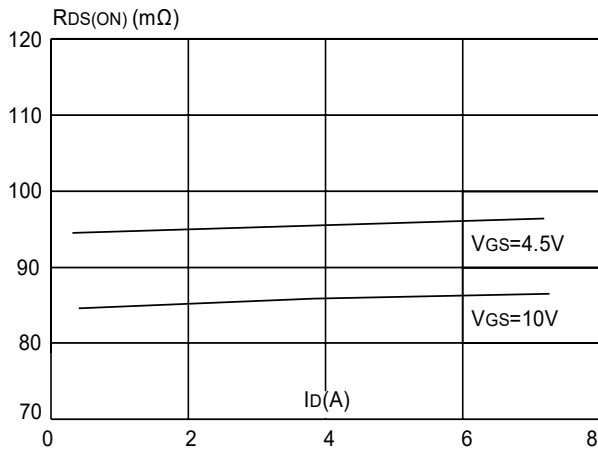


Figure 4: Body Diode Characteristics

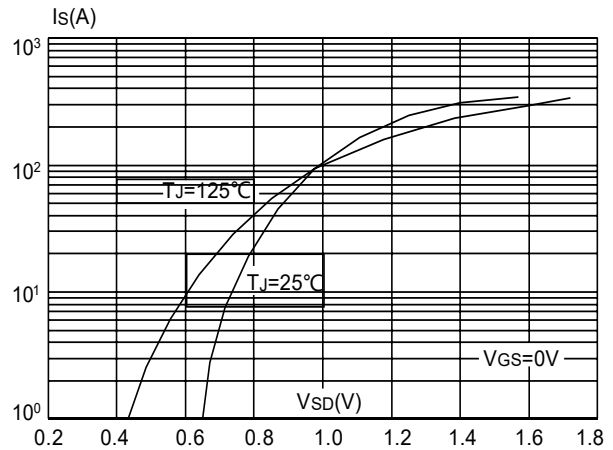


Figure 5: Gate Charge Characteristics

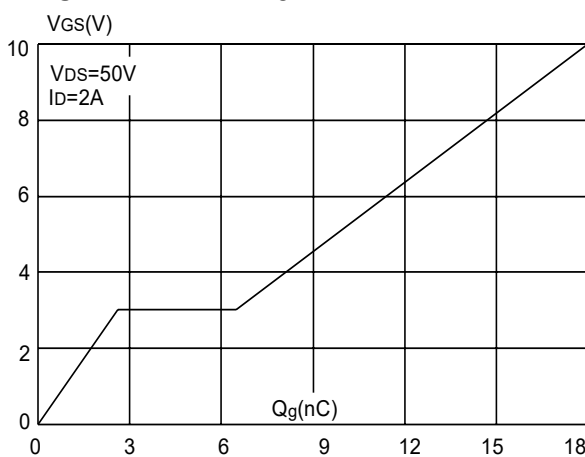


Figure 6: Capacitance Characteristics

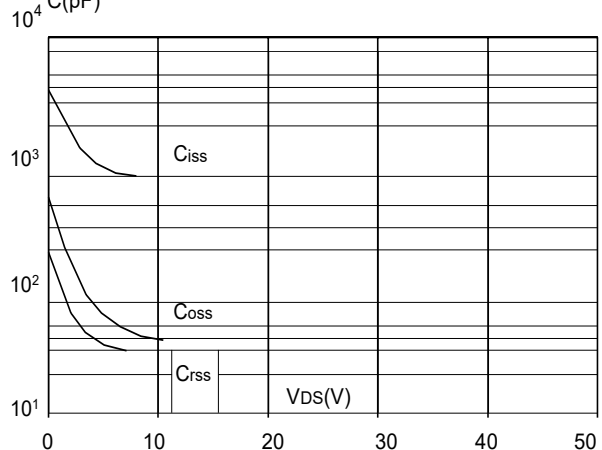




Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

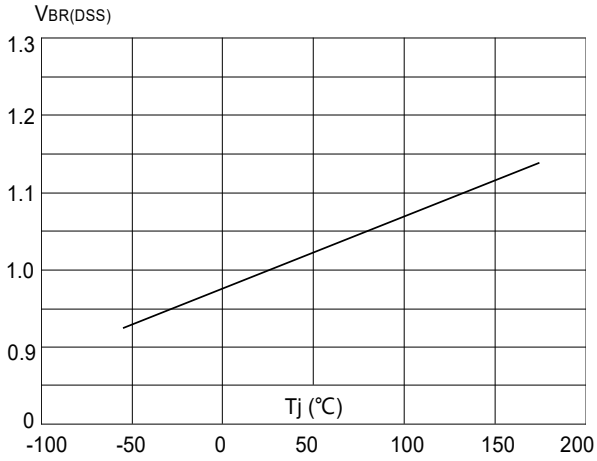


Figure 8: Normalized on Resistance vs. Junction Temperature

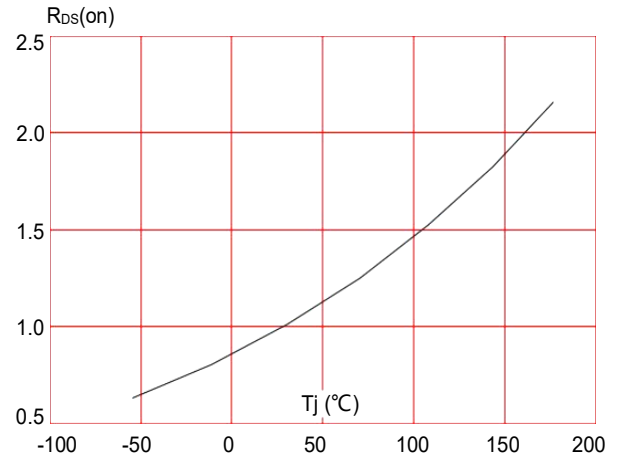


Figure 9: Maximum Safe Operating Area

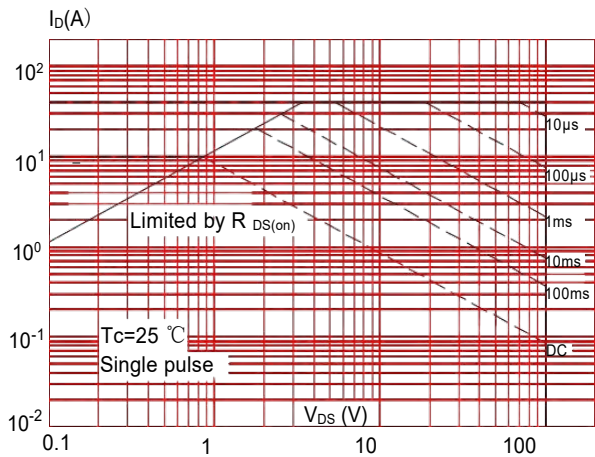


Figure 10: Maximum Continuous Drain Current vs. Case Temperature

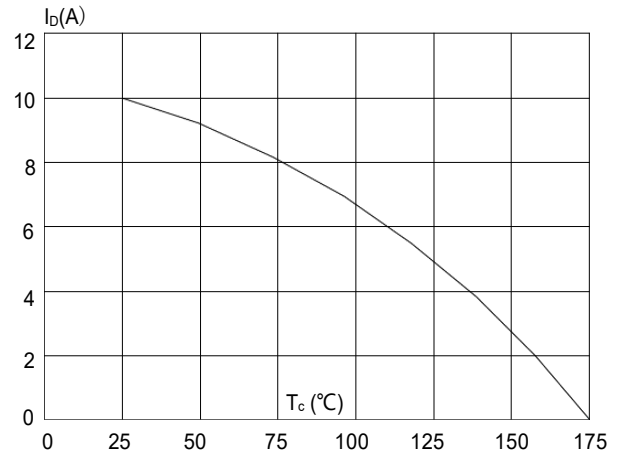
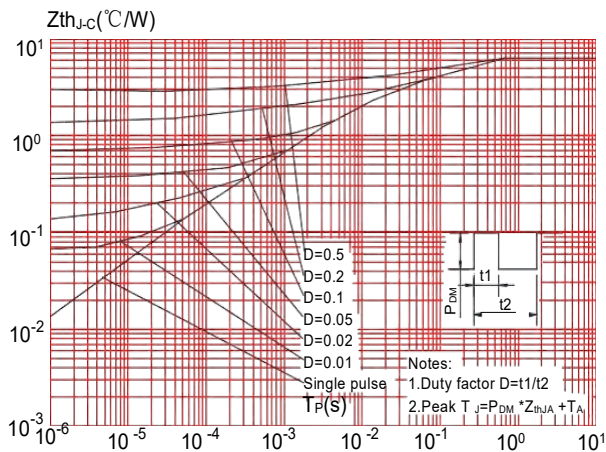
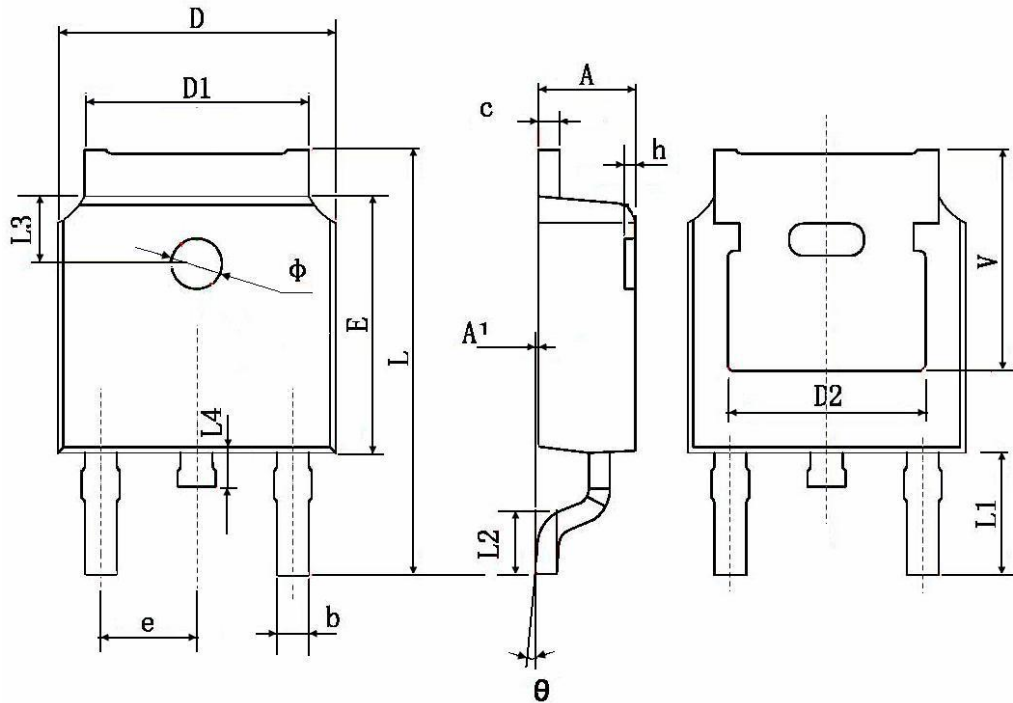


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Case





TO-252-2L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.660	0.860	0.026	0.034
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	0.483 TYP.		0.190 TYP.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.800	10.400	0.386	0.409
L1	2.900 TYP.		0.114 TYP.	
L2	1.400	1.700	0.055	0.067
L3	1.600 TYP.		0.063 TYP.	
L4	0.600	1.000	0.024	0.039
Φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.350 TYP.		0.211 TYP.	



Attention

- Any and all HUA XUAN YANG ELECTRONICS products described or contained herein do not have specifications that can handle applications that require extremely high levels of reliability, such as life-support systems, aircraft's control systems, or other applications whose failure can be reasonably expected to result in serious physical and/or material damage. Consult with your HUA XUAN YANG ELECTRONICS representative nearest you before using any HUA XUAN YANG ELECTRONICS products described or contained herein in such applications.
- HUA XUAN YANG ELECTRONICS assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all HUA XUAN YANG ELECTRONICS products described or contained herein.
- Specifications of any and all HUA XUAN YANG ELECTRONICS products described or contained herein stipulate the performance, characteristics, and functions of the described products in the independent state, and are not guarantees of the performance, characteristics, and functions of the described products as mounted in the customer's products or equipment. To verify symptoms and states that cannot be evaluated in an independent device, the customer should always evaluate and test devices mounted in the customer's products or equipment.
- HUA XUAN YANG ELECTRONICS CO.,LTD. strives to supply high-quality high-reliability products. However, any and all semiconductor products fail with some probability. It is possible that these probabilistic failures could give rise to accidents or events that could endanger human lives, that could give rise to smoke or fire, or that could cause damage to other property. When designing equipment, adopt safety measures so that these kinds of accidents or events cannot occur. Such measures include but are not limited to protective circuits and error prevention circuits for safe design, redundant design, and structural design.
- In the event that any or all HUA XUAN YANG ELECTRONICS products(including technical data, services) described or contained herein are controlled under any of applicable local export control laws and regulations, such products must not be exported without obtaining the export license from the authorities concerned in accordance with the above law.
- No part of this publication may be reproduced or transmitted in any form or by any means, electronic or mechanical, including photocopying and recording, or any information storage or retrieval system, or otherwise, without the prior written permission of HUA XUAN YANG ELECTRONICS CO.,LTD.
- Information (including circuit diagrams and circuit parameters) herein is for example only ; it is not guaranteed for volume production. HUA XUAN YANG ELECTRONICS believes information herein is accurate and reliable, but no guarantees are made or implied regarding its use or any infringements of intellectual property rights or other rights of third parties.
- Any and all information described or contained herein are subject to change without notice due to product/technology improvement, etc. When designing equipment, refer to the "Delivery Specification" for the HUA XUAN YANG ELECTRONICS product that you intend to use.